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<input type="checkbox"/>	L16	(gate with width) same (photolithograph\$2 or lithograph\$2) and ((pattern or mask) with overlap\$4)	201
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<input type="checkbox"/>	L14	L13 and (limit\$7 with (wavelength with CD or width or dimension))	300
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<input type="checkbox"/>	L9	L8 and ((width or dimension) with (less or lower or below) with limit)	179
<input type="checkbox"/>	L8	L7 and (limit\$6 same (photolithograph\$2 or lithograph\$2))	3411
<input type="checkbox"/>	L7	L6 and (pattern\$4 same (resist or photoresist))	9430
<input type="checkbox"/>	L6	L5 not L4	27763
<input type="checkbox"/>	L5	((critical adj dimension) or CD or (gate with width) or (line with width)) same (wavelength or photolithograp\$8 or lithograp\$8)	27980
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<input type="checkbox"/>	L4	(L1 or L2 or L3) and ((critical adj dimension) or CD or (gate with width) or (line with width)) and (photolithograp\$8 or lithograp\$8)	437
<input type="checkbox"/>	L3	438/588.ccls.	222
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1. Patterning sub-30-nm MOSFET gate with l-line lithography

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